

IGBT3 Chip

Features:

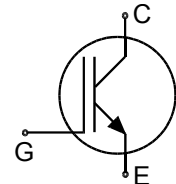
- 1200V Trench & Field Stop technology
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

This chip is used for:

- power modules

Applications:

- drives



Chip Type	V _{CE}	I _C	Die Size	Package
SIGC57T120R3LE	1200V	50A	7.6 x 7.53 mm ²	sawn on foil

Mechanical Parameters

Raster size	7.6 x 7.53	mm ²
Emitter pad size (incl. gate pad)	4x(2.98 x 2.97)	
Gate pad size	1.139 x 1.139	
Area total	57.2	
Thickness	120	µm
Wafer size	200	mm
Max.possible chips per wafer	458	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject ink dot size	Ø 0.65mm ; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C	



SIGC57T120R3LE

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter voltage, $T_{vj} = 25\text{ °C}$	V_{CE}	1200	V
DC collector current, limited by $T_{vj\text{ max}}$	I_C	¹⁾	A
Pulsed collector current, t_p limited by $T_{vj\text{ max}}$	$I_{C,puls}$	150	A
Gate emitter voltage	V_{GE}	±20	V
Junction temperature range	T_{vj}	-55 ... +175	°C
Operating junction temperature	T_{vj}	-55...+150	°C
Short circuit data ²⁾ $V_{GE} = 15V, V_{CC} = 900V, T_{vj} = 125\text{ °C}$	t_{SC}	10	µs
Reverse bias safe operating area ²⁾ (RBSOA)	$I_{C,max} = 100A, V_{CE,max} = 1200V$ $T_{vj} \leq 125\text{ °C}$		

¹⁾ depending on thermal properties of assembly

²⁾ not subject to production test - verified by design/characterization

Static Characteristic (tested on wafer), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=2mA$	1200			V
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE}=15V, I_C=50A$	1.4	1.7	2.1	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=2mA, V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$			6.79	µA
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$			600	nA
Integrated gate resistor	r_G			4		Ω

Dynamic Characteristic (not subject to production test - verified by design / characterization), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{ies}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$		3600		pF
Reverse transfer capacitance	C_{res}			163		



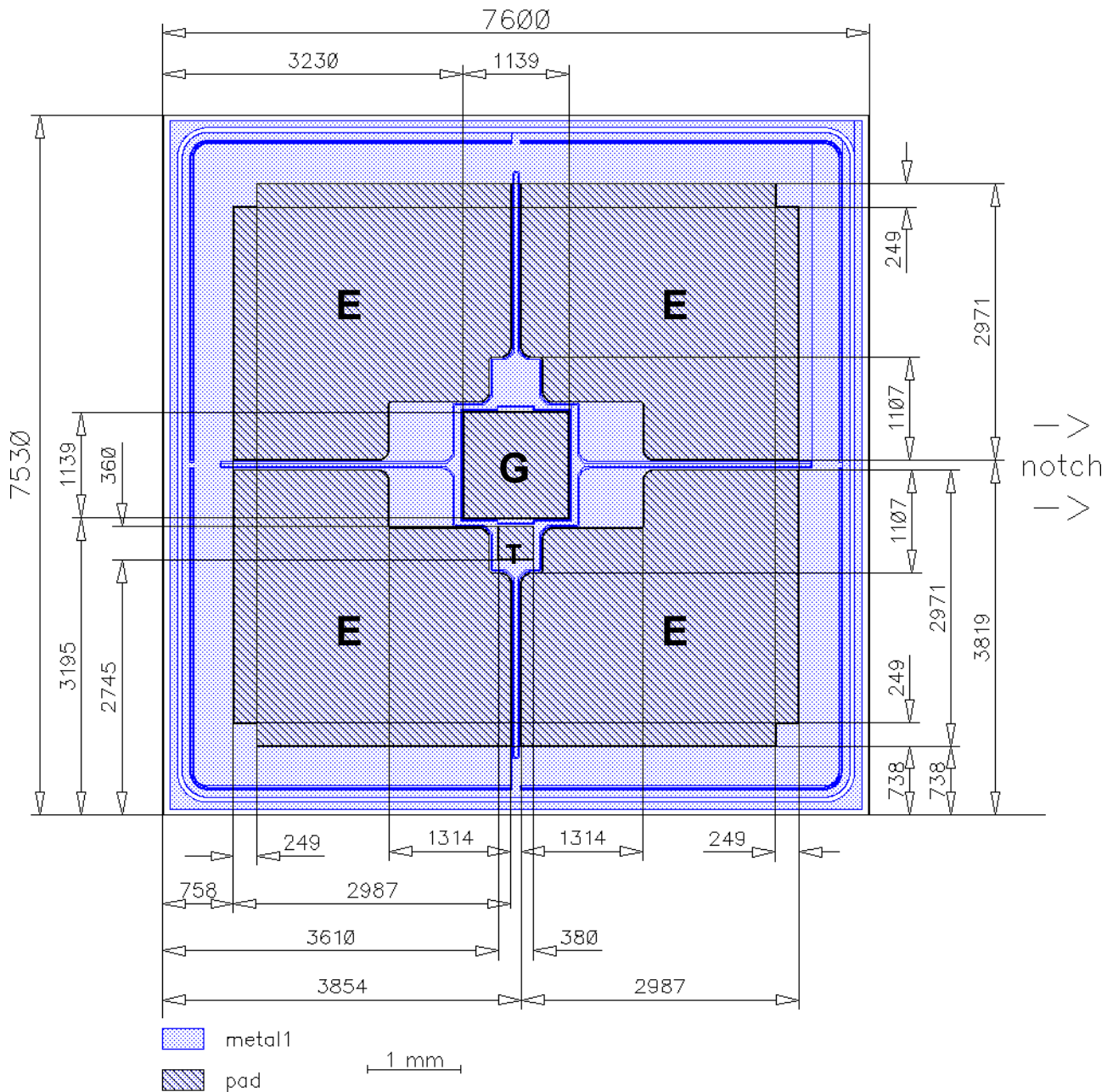
SIGC57T120R3LE

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Chip Drawing

Die-Size 7600 um x 7530 um



E = Emitter

G = Gate

T = Test pad do not contact



SIGC57T120R3LE

Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date
2.2	Change wafer size to 200 mm	30.04.2010

Published by
Infineon Technologies AG
81726 Munich, Germany
© 2010 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.